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SC 1690

U.S. UTILITY Patent Application

PATENT NUMBER and
ISSUE DATE

APPL NUM 10050570	FILING DATE 01/18/2002	CLASS 117	SUBCLASS	GAU 1765	EXAMINER SONG
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**APPLICANTS:
Yagi Kuniaki; Nagasawa Hiroyuki;

**CONTINUING DATA VERIFIED:
none

** FOREIGN APPLICATIONS VERIFIED:
JAPAN 11312/2001 01/19/2001 M)

PG-PUB DO NOT PUBLISH ☐

RESCIND ☐

Foreign priority claimed ☐ yes ☐ no
35 USC 119 conditions met ☒ yes ☐ no
Verified and Acknowledged Examiners's initials M

ATTORNEY DOCKET NO

Q68148

TITLE : Single crystal SiCand method of producing the same as well as SiC semiconductor device and
SiC composite material

U.S. DEPT. OF COMM./PAT. & TM.-PTO-438L (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
ISSUE FEE			Total Claims	Print Claim for O.G.
Amount Due	Date Paid	Primary Examiner	DRAWING	
<input type="checkbox"/> TERMINAL DISCLAIMER			Sheets Drwg.	Figs. Drwg.
		Application Examiner		
PREPARED FOR ISSUE		WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.		

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